

KEC

SEMICONDUCTOR
TECHNICAL DATA

KDV142EL

SILICON EPITAXIAL PIN TYPE DIODE

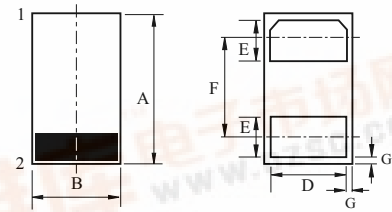
For antenna switches in mobile applications.

FEATURES

- Low Capacitance : $C_T=0.35[\text{pF}]$ (Max.)
- Low Series resistance : $r_s=1.3[\Omega]$ (Max.)
- Small Package .

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	30	V
Forward Current	I_F	100	mA
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 ~ 150	℃



DIM	MILLIMETERS
A	0.6 ± 0.03
B	0.3 ± 0.03
C	0.28 ± 0.03
D	0.25 ± 0.02
E	0.18 ± 0.02
F	Typ 0.37
G	0.025 ± 0.015

ELP-2

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ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Current	I_R	$V_R=30\text{V}$	-	-	0.1	μA
Forward Voltage	V_F	$I_F=10\text{mA}$	-	-	1.0	V
Total Capacitance	C_T	$V_R=1\text{V}$, $f=1\text{MHz}$	-	-	0.35	pF
Series Resistance	r_s	$I_F=10\text{mA}$, $f=100\text{MHz}$	-	-	1.3	Ω
ESD-Capability *	-	$C=200\text{pF}$, $R=0\Omega$, Both forward and reverse direction 1 pulse	100	-	-	V

* Failure criterion : $I_R > 100\text{nA}$ at $V_R=30\text{V}$.

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